

Analysis of Re-SiC

Item	Unit	Index
Application temperature	°C	1650(Oxidising temperature)
	°C	2300(Inert atmosphere)
Density	g/cm ³	≥ 2.75
Open porosity	%	≤ 15
Bending strength	Mpa	80-100 (20°C)
	Mpa	100-120(1100°C)
Thermal conductivity	W/m.k	26(1200°C)
Thermal expansion(20-1200°C)	K-1×10-6	4.8
Young's modules at 20°C	GPa	280
Acid and alkali resistance		Excellent
SiC	%	>98.5
C	%	<1.5